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(54) Control device for double gate semiconductor device

(57) A control device (20) includes a first gate control circuit (21) for supplying a control signal from a control signal inputted to an input terminal P1 to a gate G1, and a second gate control circuit (22) for supplying a control signal from a control signal inputted to the same input terminal P1 to a gate G2. The first gate control circuit (21) is provided with a delay circuit (31), and after a turn-off signal is supplied to the gate G2 for the transition from a thyristor condition to a transistor condition, a turn-off signal is supplied to the gate G1, thereby positively stopping operation of the double gate semiconductor device.

cuit (21) is provided with a delay circuit (31), and after a turn-off signal is supplied to the gate G2 for the transition from a thyristor condition to a transistor condition, a turn-off signal is supplied to the gate G1, thereby positively stopping operation of the double gate semiconductor device.

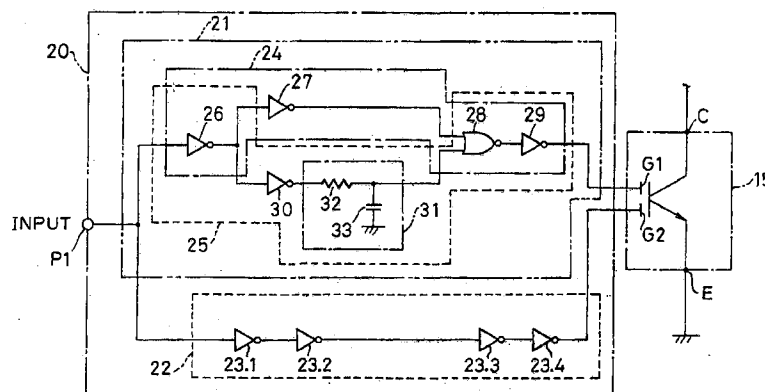


FIG.5

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EUROPEAN SEARCH REPORT

Application Number  
EP 98 20 0352

DOCUMENTS CONSIDERED TO BE RELEVANT			
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int.Cl.6)
A	US 4 792 838 A (HAYASHI YASUhide ET AL) 20 December 1988 * column 6, line 19 - column 9, line 47; figures *	1,3,7	H03K17/567 H03K17/082
A	--- PATENT ABSTRACTS OF JAPAN vol. 014, no. 038 (E-878), 24 January 1990 & JP 01 270352 A (TOSHIBA CORP), 27 October 1989 * abstract *	1,7	
A	--- EP 0 463 325 A (TOKYO SHIBAURA ELECTRIC CO) 2 January 1992 * column 6, line 23 - column 7, line 53; figures *	1,7	
			TECHNICAL FIELDS SEARCHED (Int.Cl.6)
			H03K
The present search report has been drawn up for all claims			
Place of search	Date of completion of the search	Examiner	
THE HAGUE	14 October 1998	D/L PINTA BALLE., L	
CATEGORY OF CITED DOCUMENTS		T : theory or principle underlying the invention E : earlier patent document, but published on, or after the filing date D : document cited in the application L : document cited for other reasons & : member of the same patent family, corresponding document	
X : particularly relevant if taken alone Y : particularly relevant if combined with another document of the same category A : technological background O : non-written disclosure P : intermediate document			

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